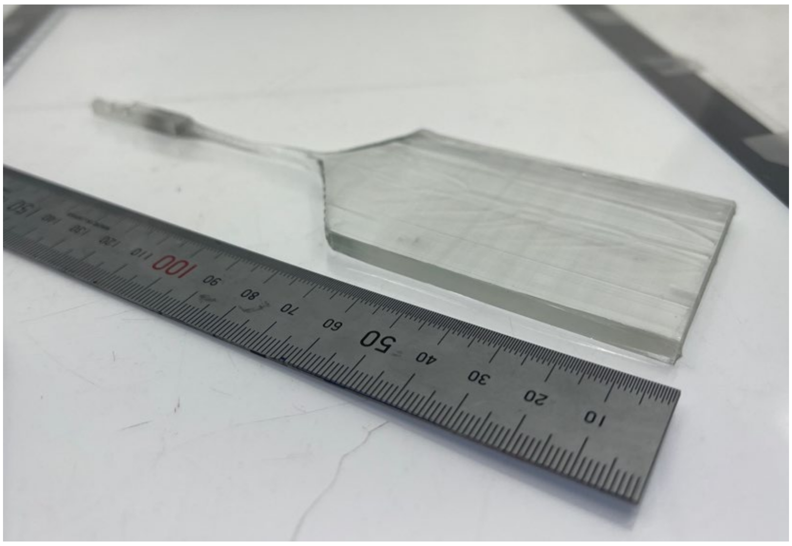
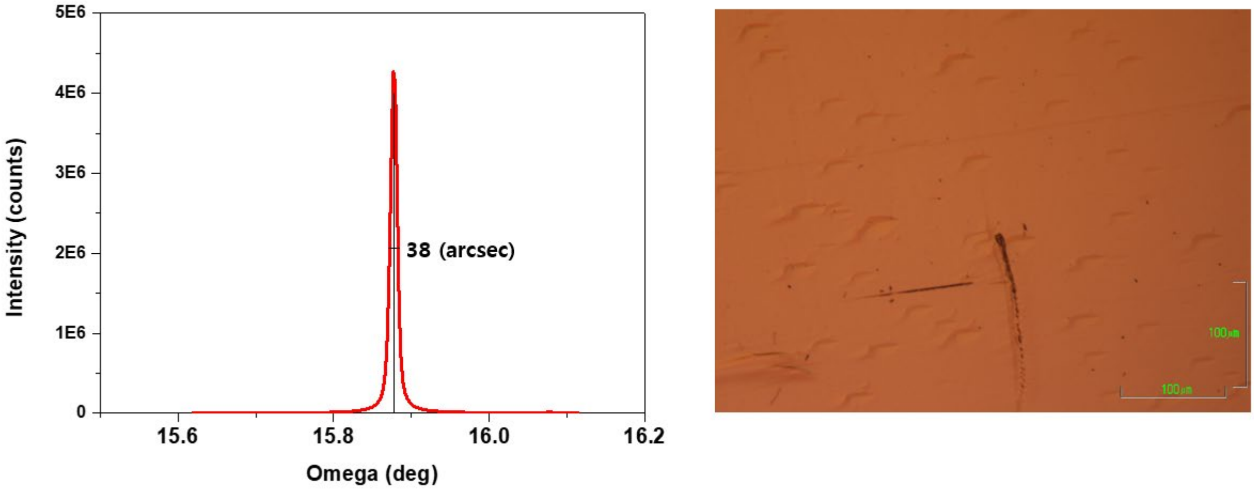


The typical bulk β-Ga_2O_3 single crystal ribbon grown by EFG method. The growth direction and the principal surface were set to be the [010] direction and the (001) plane for this β-Ga_2O_3 crystal, respectively. The ingot's body height and thickness are about 80mm and 4mm, respectively. The growth rate for this ingot is about 15mm/h.



X-ray rocking curve and etched surface of the typical bulk β-Ga_2O_3 single crystal ribbon grown by EFG method.